## EH2700ETTTS-125.000M



T TS -125.000M EH27 00 ET

> - Nominal Frequency 125.000MHz

Series -RoHS Compliant (Pb-free) 2.5V 4 Pad 5mm x 7mm Ceramic SMD LVCMOS Oscillator

Frequency Tolerance/Stability ±100ppm Maximum

Operating Temperature Range -40°C to +85°C

#### Tri-State (High Impedance) Duty Cycle 50 ±5(%)

L Pin 1 Connection

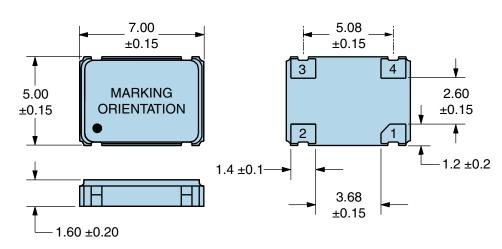
ELECTRICAL SPECIFICATIONS		
Nominal Frequency	125.000MHz	
Frequency Tolerance/Stability	±100ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over t Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°, 260°C Reflow, Shock, and Vibration)	
Aging at 25°C	±5ppm/Year Maximum	
Operating Temperature Range	-40°C to +85°C	
Supply Voltage	2.5Vdc ±5%	
Input Current	9mA Maximum (No Load)	
Output Voltage Logic High (Voh)	90% of Vdd Minimum (IOH = -8mA)	
Output Voltage Logic Low (Vol)	10% of Vdd Maximum (IOL = +8mA)	
Rise/Fall Time	2nSec Maximum (Measured at 20% to 80% of waveform)	
Duty Cycle	50 ±5(%) (Measured at 50% of waveform)	
Load Drive Capability	15pF Maximum	
Output Logic Type	CMOS	
Pin 1 Connection	Tri-State (High Impedance)	
Tri-State Input Voltage (Vih and Vil)	90% of Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High Impedance)	
Standby Current	10μA Maximum (Pin 1 = Ground)	
Absolute Clock Jitter	±100pSec Maximum	
Start Up Time	10mSec Maximum	
Storage Temperature Range	-55°C to +125°C	

## **ENVIRONMENTAL & MECHANICAL SPECIFICATIONS**

ESD Susceptibility	MIL-STD-883, Method 3015, Class 1, HBM: 1500V	
Fine Leak Test	MIL-STD-883, Method 1014, Condition A	
Flammability	UL94-V0	
Gross Leak Test	MIL-STD-883, Method 1014, Condition C	
Mechanical Shock	MIL-STD-883, Method 2002, Condition B	
Moisture Resistance	MIL-STD-883, Method 1004	
Moisture Sensitivity	J-STD-020, MSL 1	
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K	
Resistance to Solvents	MIL-STD-202, Method 215	
Solderability	MIL-STD-883, Method 2003	
Temperature Cycling	MIL-STD-883, Method 1010, Condition B	
Vibration	MIL-STD-883, Method 2007, Condition A	

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## **MECHANICAL DIMENSIONS (all dimensions in millimeters)**

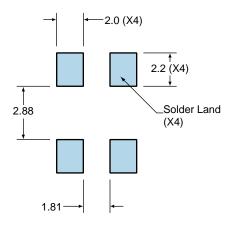


ECL	<b>IPT</b>	EK®
CORP	ORA	TION

PIN	CONNECTION
1	Tri-State
2	Case Ground
3	Output
4	Supply Voltage
LINE MARKING	
LINE	MARKING
LINE 1	MARKING ECLIPTEK

### Suggested Solder Pad Layout

All Dimensions in Millimeters

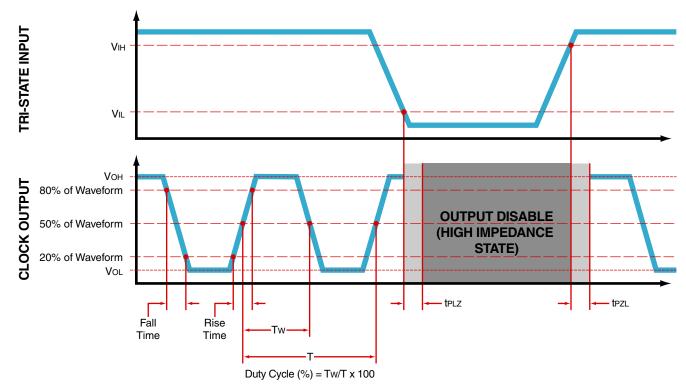


All Tolerances are ±0.1

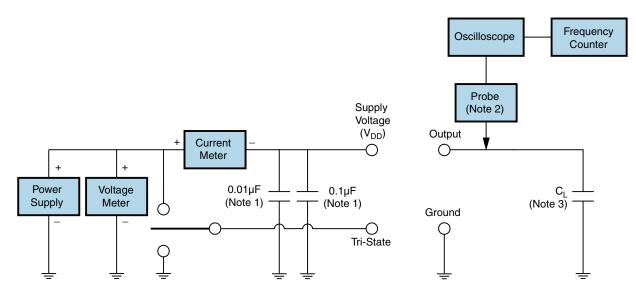
## EH2700ETTTS-125.000M



#### **OUTPUT WAVEFORM & TIMING DIAGRAM**



**Test Circuit for CMOS Output** 



- Note 1: An external 0.01µF ceramic bypass capacitor in parallel with a 0.1µF high frequency ceramic bypass capacitor close (less than 2mm) to the package ground and supply voltage pin is required.
- Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value  $C_L$  includes sum of all probe and fixture capacitance.



## **Recommended Solder Reflow Methods**

EH2700ETTTS-125.000M



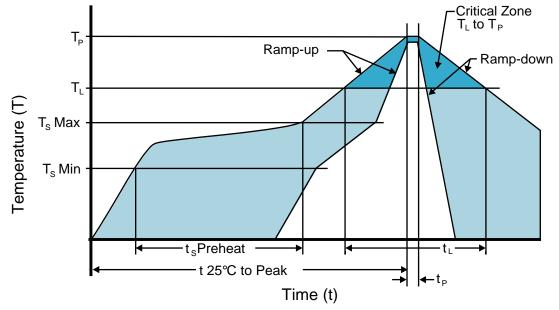
### **High Temperature Infrared/Convection**

<u> </u>	
T <sub>s</sub> MAX to T <sub>L</sub> (Ramp-up Rate)	3°C/second Maximum
Preheat	
- Temperature Minimum (T <sub>s</sub> MIN)	150°C
- Temperature Typical (T <sub>s</sub> TYP)	175°C
<ul> <li>Temperature Maximum (T<sub>s</sub> MAX)</li> </ul>	200°C
- Time (t <sub>s</sub> MIN)	60 - 180 Seconds
Ramp-up Rate (T⊾ to T <sub>P</sub> )	3°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	217°C
- Time (t∟)	60 - 150 Seconds
Peak Temperature (T <sub>P</sub> )	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T <sub>P</sub> Target)	250°C +0/-5°C
Time within 5°C of actual peak (t <sub>P</sub> )	20 - 40 seconds
Ramp-down Rate	6°C/second Maximum
Time 25°C to Peak Temperature (t)	8 minutes Maximum
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.



## **Recommended Solder Reflow Methods**

EH2700ETTTS-125.000M



### Low Temperature Infrared/Convection 240°C

$T_s$ MAX to $T_L$ (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (T <sub>s</sub> MIN)	N/A
- Temperature Typical (T <sub>s</sub> TYP)	150°C
- Temperature Maximum (T <sub>s</sub> MAX)	N/A
- Time (t <sub>s</sub> MIN)	60 - 120 Seconds
Ramp-up Rate (T⊾ to T <sub>P</sub> )	5°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T <sub>P</sub> )	240°C Maximum
Target Peak Temperature (T <sub>P</sub> Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
Time within 5°C of actual peak (t <sub>p</sub> )	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

### Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

### **High Temperature Manual Soldering**

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)